



128Kx32 SRAM/FLASH MODULE

FEATURES

- Access Times of 25ns (SRAM) and 70, 90 and 120ns (FLASH)
- Packaging:
 - 66-pin, PGA Type, 1.385 inch square HIP, Hermetic Ceramic HIP (Package 402)
- 128Kx32 SRAM
- 128Kx32 5V Flash
- Organized as 128Kx32 of SRAM and 128Kx32 of Flash Memory with common Data Bus
- Low Power CMOS
- Commercial, Industrial and Military Temperature Ranges
- TTL Compatible Inputs and Outputs
- Built-in Decoupling Caps and Multiple Ground Pins for Low Noise Operation
- Weight - 13 grams typical

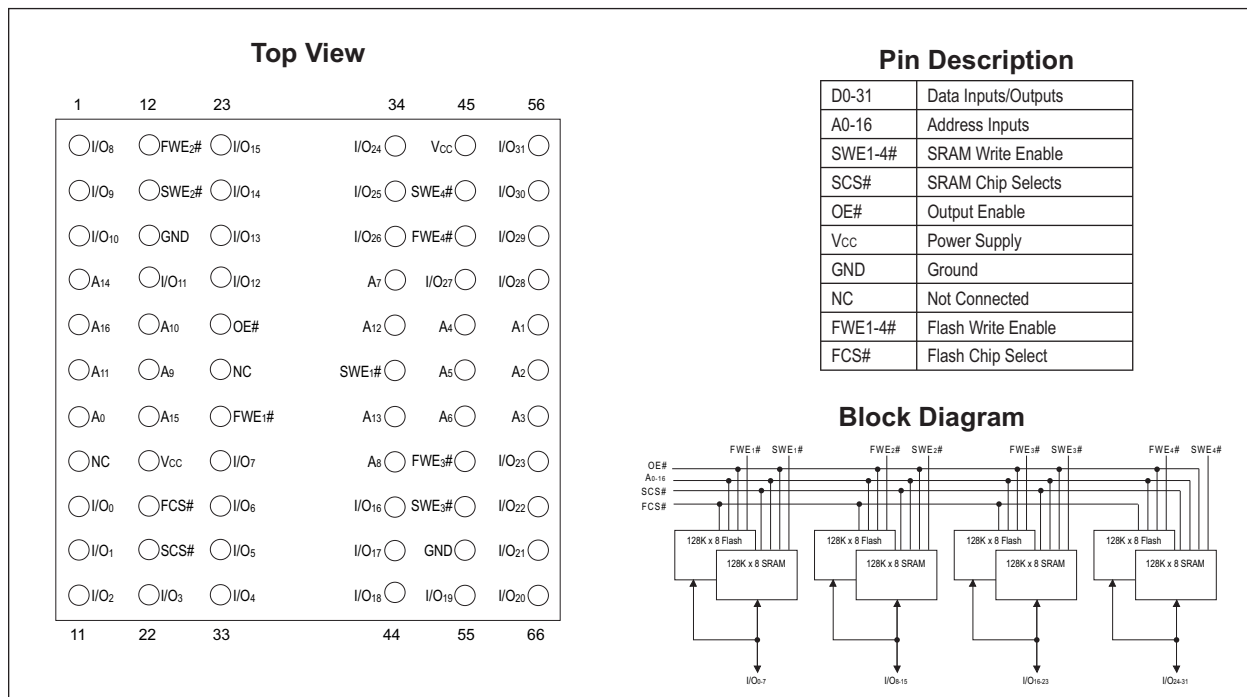
FLASH MEMORY FEATURES

- 10,000 Erase/Program Cycles
- Sector Architecture
 - 8 equal size sectors of 16K bytes each
 - Any combination of sectors can be concurrently erased. Also supports full chip erase
- 5 Volt Programming; 5V $\pm$ 10% Supply
- Embedded Erase and Program Algorithms
- Hardware Write Protection
- Page Program Operation and Internal Program Control Time.

* This product is under development, not fully characterized, and is subject to change without notice.

Note: Programming information available upon request.

FIGURE 1 – PIN CONFIGURATION FOR WSF128K32-XH2X





ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Min	Max	Unit
Operating Temperature	T _A	-55	+125	°C
Storage Temperature	T _{STG}	-65	+150	°C
Signal Voltage Relative to GND	V _G	-0.5	7.0	V
Junction Temperature	T _J		150	°C
Supply Voltage	V _{CC}	-0.5	7.0	V

Parameter	
Flash Data Retention	10 years
Flash Endurance (write/erase cycles)	10,000

NOTE:

- Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

SRAM TRUTH TABLE

SCS#	OE#	SWE#	Mode	Data I/O	Power
H	X	X	Standby	High Z	Standby
L	L	H	Read	Data Out	Active
L	H	H	Read	High Z	Active
L	X	L	Write	Data In	Active

NOTE:

- FCS# must remain high when SCS# is low.

CAPACITANCE

T_a = +25°C

Parameter	Symbol	Conditions	Max	Unit
OE# capacitance	C _{OE}	V _{IN} = 0 V, f = 1.0 MHz	80	pF
F/S WE ₁₋₄ # capacitance	C _{WE}	V _{IN} = 0 V, f = 1.0 MHz	30	pF
F/S CS# capacitance	C _{CS}	V _{IN} = 0 V, f = 1.0 MHz	50	pF
D ₀₋₃₁ capacitance	C _{I/O}	V _{IN} = 0 V, f = 1.0 MHz	30	pF
A ₀₋₁₆ capacitance	C _{AD}	V _{IN} = 0 V, f = 1.0 MHz	80	pF

This parameter is guaranteed by design but not tested.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V _{CC}	4.5	5.5	V
Input High Voltage	V _{IH}	2.2	V _{CC} + 0.3	V
Input Low Voltage	V _{IL}	-0.5	+0.8	V

DC CHARACTERISTICS

V_{CC} = 5.0V, V_{SS} = 0V, -55°C ≤ T_A ≤ +125°C

Parameter	Symbol	Conditions	Min	Max	Unit
Input Leakage Current	I _{LI}	V _{CC} = 5.5, V _{IN} = GND to V _{CC}		10	μA
Output Leakage Current	I _{LO}	SCS# = V _{IH} , OE# = V _{IH} , V _{OUT} = GND to V _{CC}		10	μA
SRAM Operating Supply Current x 32 Mode	I _{CCx32}	SCS# = V _{IL} , OE# = FCS# = V _{IH} , f = 5MHz, V _{CC} = 5.5		670	mA
Standby Current	I _{SB}	FCS# = SCS# = V _{IH} , OE# = V _{IH} , f = 5MHz, V _{CC} = 5.5		80	mA
SRAM Output Low Voltage	V _{OL}	I _{OL} = 8mA, V _{CC} = 4.5		0.4	V
SRAM Output High Voltage	V _{OH}	I _{OH} = -4.0mA, V _{CC} = 4.5	2.4		V
Flash V _{CC} Active Current for Read (1)	I _{CC1}	FCS# = V _{IL} , OE# = SCS# = V _{IH}		220	mA
Flash V _{CC} Active Current for Program or Erase (2)	I _{CC2}	FCS# = V _{IL} , OE# = SCS# = V _{IH}		280	mA
Flash Output Low Voltage	V _{OL}	I _{OL} = 8.0mA, V _{CC} = 4.5		0.45	V
Flash Output High Voltage	V _{OH1}	I _{OH} = -2.5 mA, V _{CC} = 4.5	0.85 x V _{CC}		V
Flash Output High Voltage	V _{OH2}	I _{OH} = -100 μA, V _{CC} = 4.5	V _{CC} - 0.4		V
Flash Low V _{CC} Lock Out Voltage	V _{LKO}		3.2		V

NOTES:

- The I_{CC} current listed includes both the DC operating current and the frequency dependent component (@ 5 MHz).
The frequency component typically is less than 2 mA/MHz, with OE# at V_{IH}.
- I_{CC} active while Embedded Algorithm (program or erase) is in progress.
- DC test conditions: V_{IL} = 0.3V, V_{IH} = V_{CC} - 0.3V



SRAM AC CHARACTERISTICS

$V_{CC} = 5.0V$, $-55^{\circ}C \leq T_A \leq +125^{\circ}C$

Parameter Read Cycle	Symbol	-25		Units
		Min	Max	
Read Cycle Time	t_{RC}	25		ns
Address Access Time	t_{AA}		25	ns
Output Hold from Address Change	t_{OH}	0		ns
Chip Select Access Time	t_{ACS}		25	ns
Output Enable to Output Valid	t_{OE}		15	ns
Chip Select to Output in Low Z	t_{CLZ}^1	3		ns
Output Enable to Output in Low Z	t_{OLZ}^1	0		ns
Chip Disable to Output in High Z	t_{CHZ}^1		12	ns
Output Disable to Output in High Z	t_{OHZ}^1		12	ns

1. This parameter is guaranteed by design but not tested.

SRAM AC CHARACTERISTICS

$V_{CC} = 5.0V$, $-55^{\circ}C \leq T_A \leq +125^{\circ}C$

Parameter Write Cycle	Symbol	-25		Units
		Min	Max	
Write Cycle Time	t_{WC}	25		ns
Chip Select to End of Write	t_{CW}	20		ns
Address Valid to End of Write	t_{AW}	20		ns
Data Valid to End of Write	t_{DW}	15		ns
Write Pulse Width	t_{WP}	20		ns
Address Setup Time	t_{AS}	3		ns
Address Hold Time	t_{AH}	0		ns
Output Active from End of Write	t_{OW}^1	3		ns
Write Enable to Output in High Z	t_{WHZ}^1		15	ns
Data Hold from Write Time	t_{DH}	0		ns

1. This parameter is guaranteed by design but not tested.

FIGURE 2 – AC TEST CIRCUIT

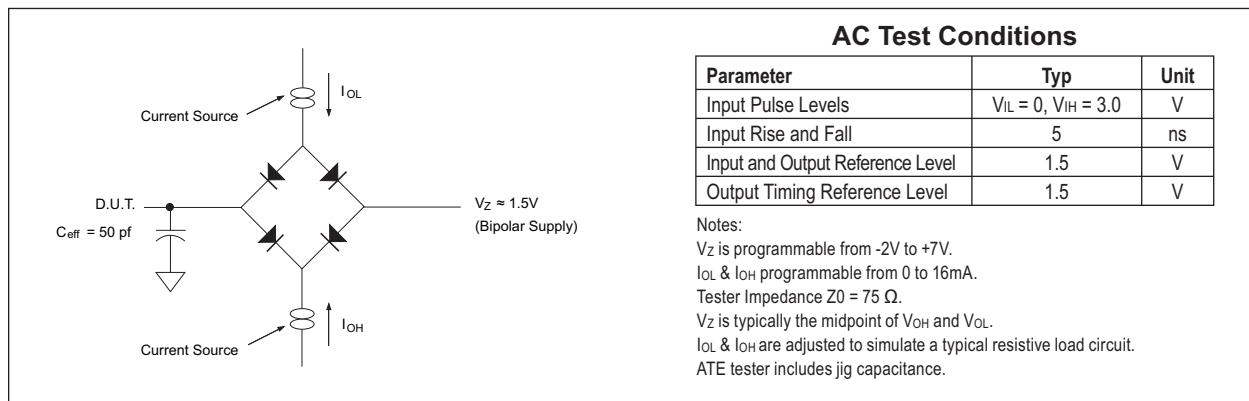




FIGURE 3 – SRAM TIMING WAVEFORM - READ CYCLE

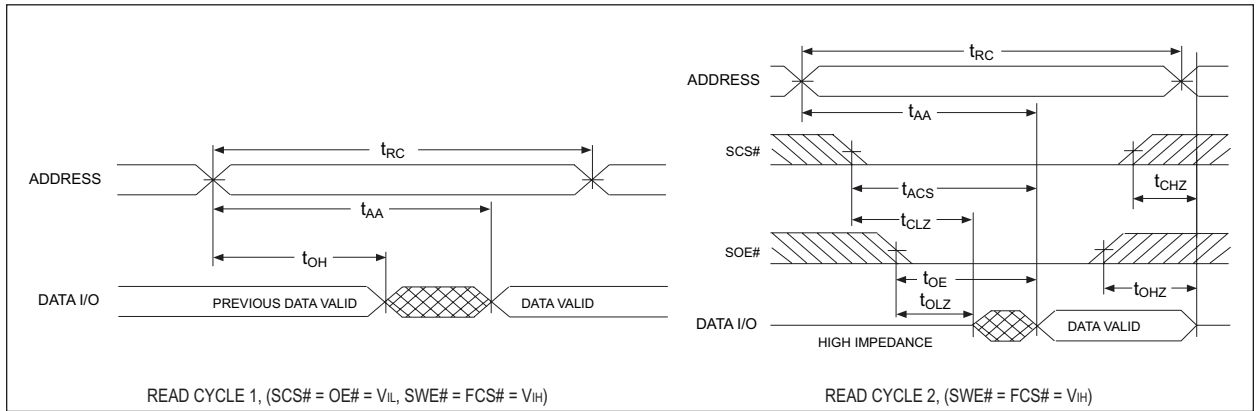


FIGURE 4 – SRAM WRITE CYCLE - SWE# CONTROLLED

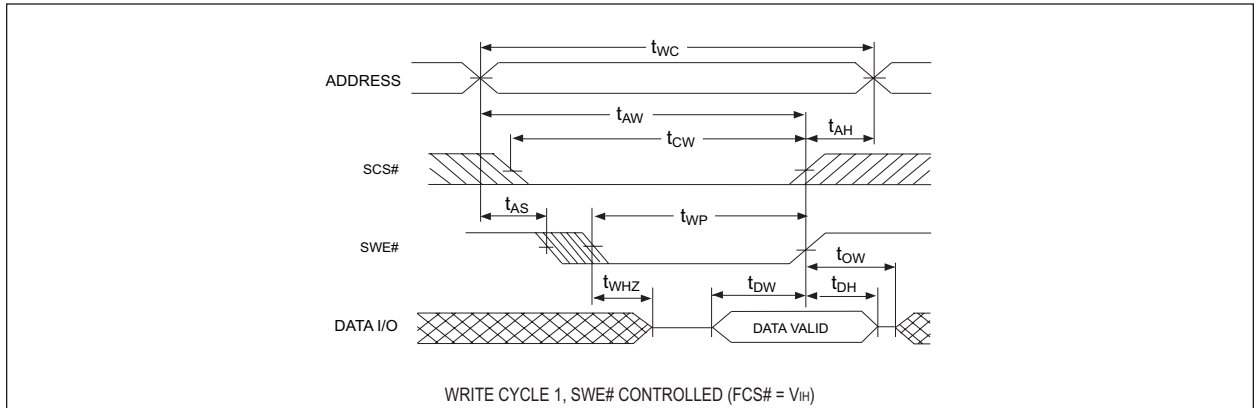
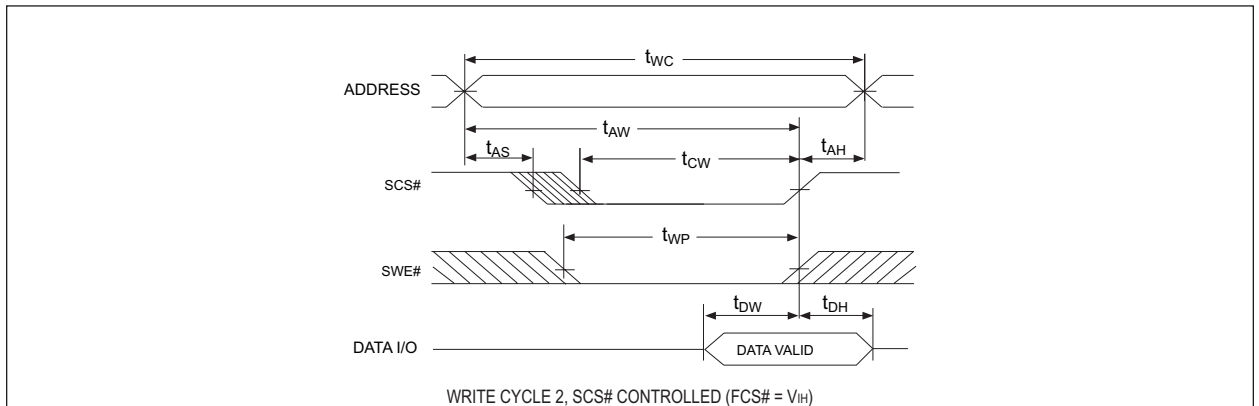


FIGURE 5 – SRAM WRITE CYCLE - SCS# CONTROLLED





FLASH AC CHARACTERISTICS – WRITE/ERASE/PROGRAM OPERATIONS, FWE# CONTROLLED

$V_{CC} = 5.0V$, $-55^{\circ}C \leq T_A \leq +125^{\circ}C$

Parameter	Symbol		-70		-90		-120		Unit
			Min	Max	Min	Max	Min	Max	
Write Cycle Time	t _{AVAV}	t _{WC}	70		90		120		ns
Chip Select Setup Time	t _{ELWL}	t _{CS}	0		0		0		ns
Write Enable Pulse Width	t _{WLWH}	t _{WP}	45		45		50		ns
Address Setup Time	t _{AVWL}	t _{AS}	0		0		0		ns
Data Setup Time	t _{DVWH}	t _{DS}	45		45		50		ns
Data Hold Time	t _{WHDX}	t _{DH}	0		0		0		ns
Address Hold Time	t _{WLAX}	t _{AH}	45		45		50		ns
Chip Select Hold Time	t _{WHEH}	t _{CH}	0		0		0		ns
Write Enable Pulse Width High	t _{WHWL}	t _{WPH}	20		20		20		ns
Duration of Byte Programming Operation (min)	t _{WHWH1}		14		14		14		μs
Chip and Sector Erase Time	t _{WHWH2}		2.2	60	2.2	60	2.2	60	sec
Read Recovery Time Before Write	t _{GHWL}		0		0		0		μs
V _{CC} Set-up Time		t _{VCS}	50		50		50		μs
Chip Programming Time				12.5		12.5		12.5	sec
Output Enable Setup Time		t _{OES}	0		0		0		ns
Output Enable Hold Time (1)		t _{OEH}	10		10		10		ns

1. For Toggle and Data# Polling.

FLASH AC CHARACTERISTICS – READ ONLY OPERATIONS

$V_{CC} = 5.0V$, $-55^{\circ}C \leq T_A \leq +125^{\circ}C$

Parameter	Symbol		-70		-90		-120		Unit
			Min	Max	Min	Max	Min	Max	
Read Cycle Time	t _{AVAV}	t _{RC}	70		90		120		ns
Address Access Time	t _{AVQV}	t _{ACC}		70		90		120	ns
Chip Select Access Time	t _{ELQV}	t _{CE}		70		90		120	ns
OE# to Output Valid	t _{GLQV}	t _{OE}		35		40		50	ns
Chip Select to Output High Z (1)	t _{EHQZ}	t _{DF}		20		25		30	ns
OE# High to Output High Z (1)	t _{GHQZ}	t _{DF}		20		25		30	ns
Output Hold from Address, FCS# or OE# Change, whichever is first	t _{AXQX}	t _{OH}	0		0		0		ns

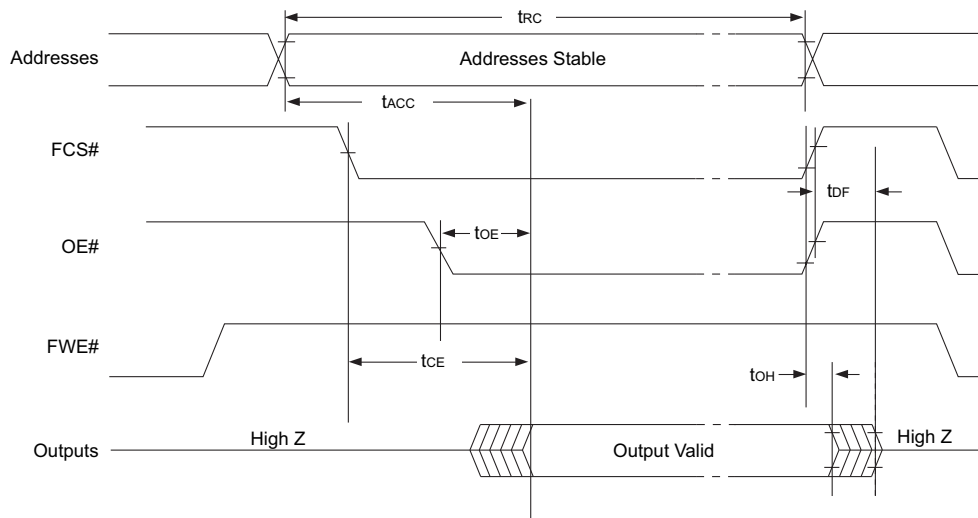
1. Guaranteed by design, not tested.

**FLASH AC CHARACTERISTICS – WRITE/ERASE/PROGRAM OPERATIONS, FCS# CONTROLLED** $V_{CC} = 5.0V, -55^{\circ}C \leq T_A \leq +125^{\circ}C$

Parameter	Symbol		-70		-90		-120		Unit
			Min	Max	Min	Max	Min	Max	
Write Cycle Time	t _{WAV}	t _{WC}	70		90		120		ns
FWE# Setup Time	t _{WLEL}	t _{WS}	0		0		0		ns
FCS# Pulse Width	t _{LEH}	t _{CP}	35		45		50		ns
Address Setup Time	t _{AVEL}	t _{AS}	0		0		0		ns
Data Setup Time	t _{DVEH}	t _{DS}	30		45		50		ns
Data Hold Time	t _{EDX}	t _{DH}	0		0		0		ns
Address Hold Time	t _{ELAX}	t _{AH}	45		45		50		ns
FWE# Hold from FWE# High	t _{EHWH}	t _{WH}	0		0		0		ns
FCS# Pulse Width High	t _{EHEL}	t _{CPH}	20		20		20		ns
Duration of Programming Operation	t _{WHWH1}		14		14		14		μs
Duration of Erase Operation	t _{WHWH2}		2.2	60	2.2	60	2.2	60	sec
Read Recovery before Write	t _{GHEL}		0		0		0		ns
Chip Programming Time				12.5		12.5		12.5	sec



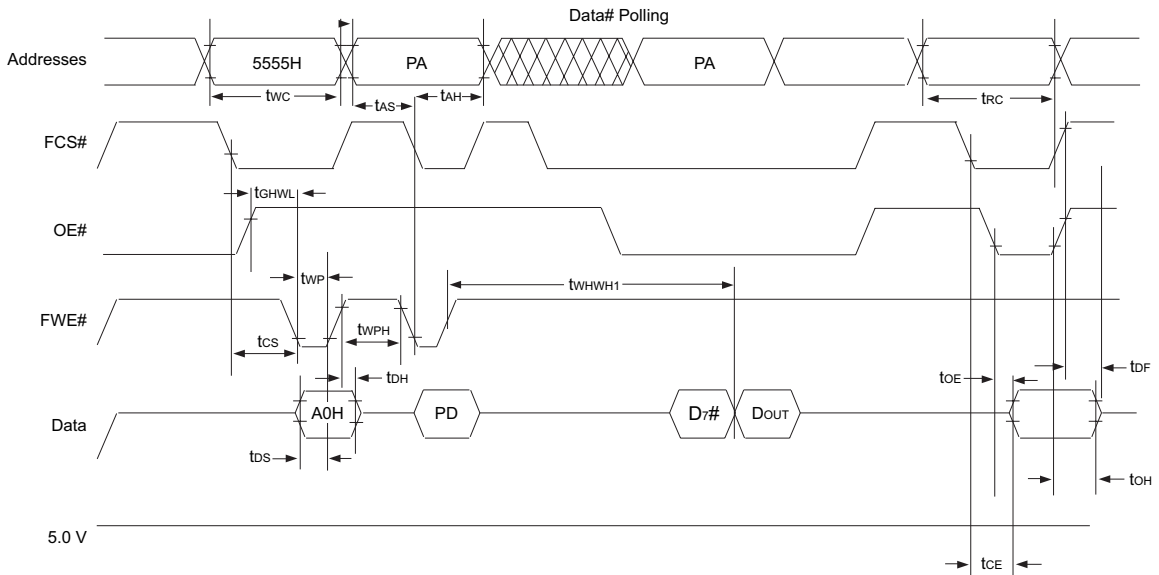
FIGURE 6 – AC WAVEFORMS FOR FLASH MEMORY READ OPERATIONS



NOTE: SCS# = V_{IH}



FIGURE 7 – WRITE/ERASE/PROGRAM OPERATION, FLASH MEMORY FWE# CONTROLLED

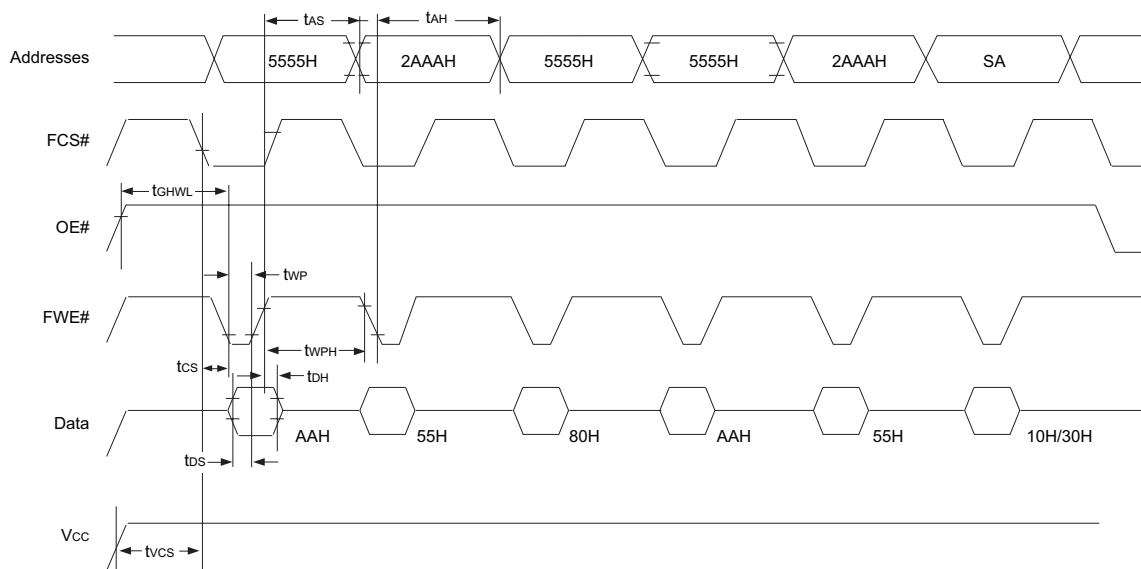


NOTES:

1. PA is the address of the memory location to be programmed.
2. PD is the data to be programmed at byte address.
3. D7# is the output of the complement of the data written to the device.
4. DOUT is the output of the data written to the device.
5. Figure indicates last two bus cycles of four bus cycle sequence.
6. SCS# = V_{IH}



FIGURE 8 – AC WAVEFORMS CHIP/SECTOR ERASE OPERATIONS FOR FLASH MEMORY

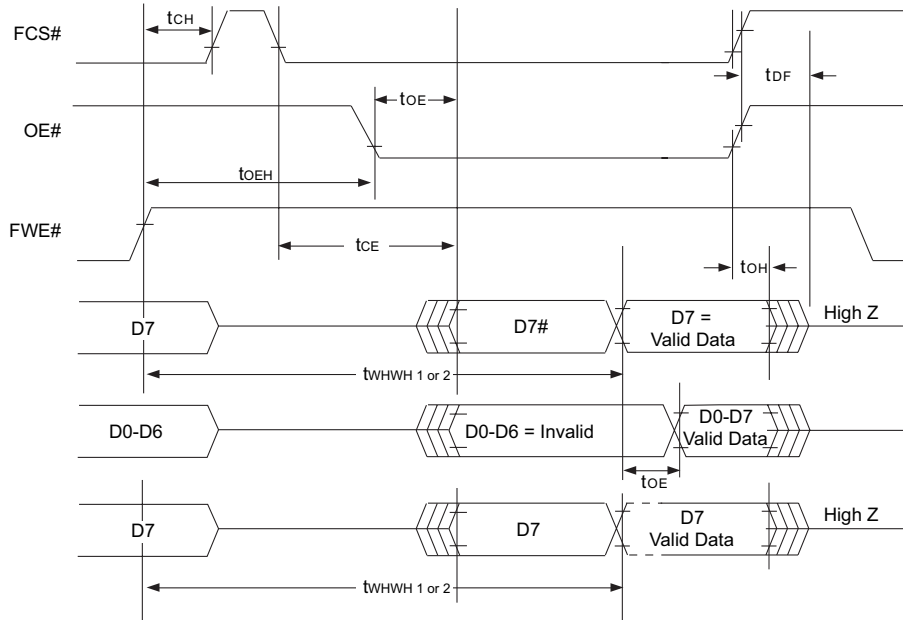


Notes:

1. SA is the sector address for Sector Erase.
2. SCS# = V_{IH}



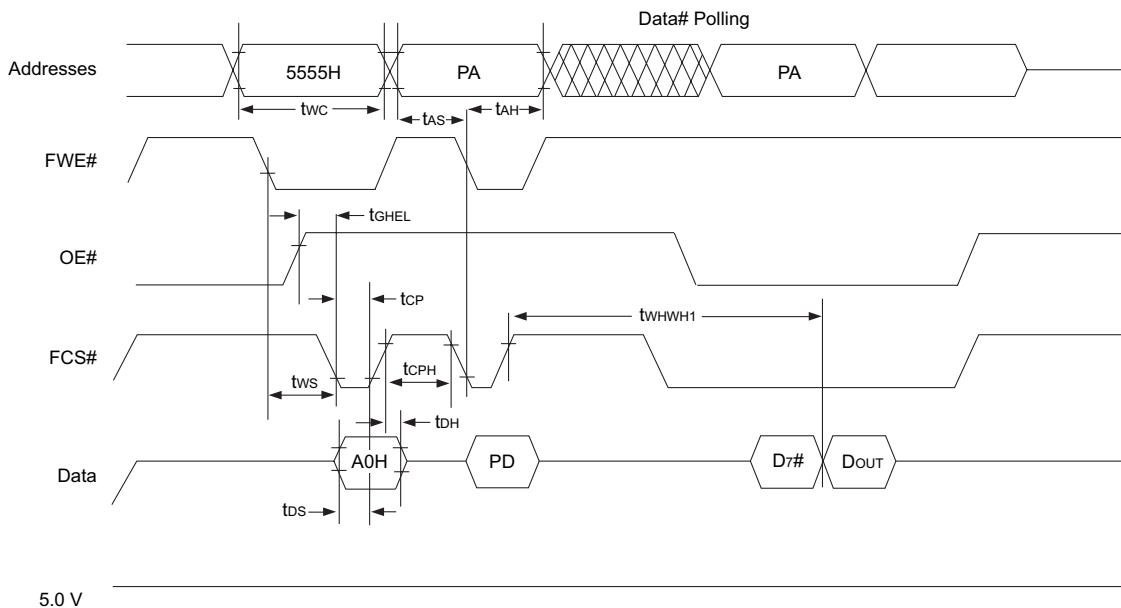
FIGURE 9 – AC WAVEFORMS FOR DATA# POLLING DURING EMBEDDED ALGORITHM OPERATIONS FOR FLASH MEMORY



Note: SCS# = V_{IH}



FIGURE 10 – WRITE/ERASE/PROGRAM OPERATION FOR FLASH MEMORY, CS# CONTROLLED

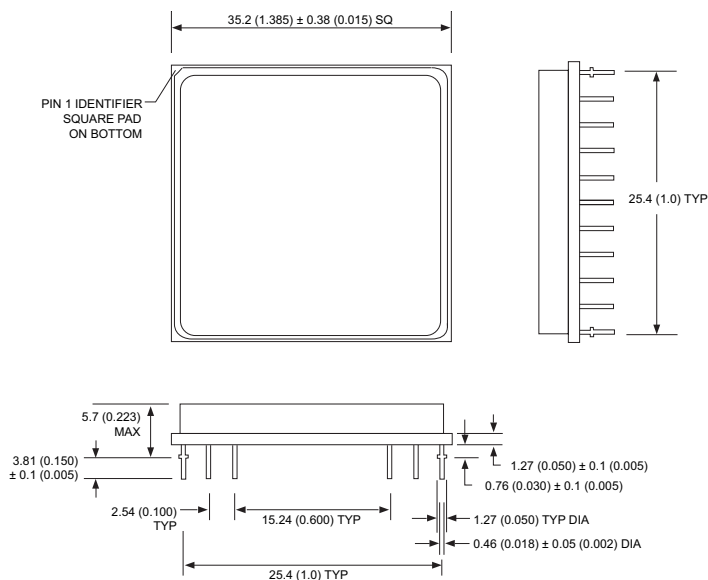


NOTES:

1. PA represents the address of the memory location to be programmed.
2. PD represents the data to be programmed at byte address.
3. D7# is the output of the complement of the data written to the device.
4. DOUT is the output of the data written to the device.
5. Figure indicates the last two bus cycles of a four bus cycle sequence.
6. SCS# = V_{IH}



PACKAGE 402: 66 PIN, PGA TYPE, CERAMIC HEX-IN-LINE PACKAGE, HIP (H2)



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

ORDERING INFORMATION

W S F 128K32 - XX H2 X X

LEAD FINISH:

Blank = Gold plated leads
A = Solder dip leads

DEVICE GRADE:

M = Military Screened -55°C to +125°C
I = Industrial -40°C to +85°C
C = Commercial 0°C to +70°C

PACKAGE TYPE:

H2 = Ceramic Hex In-line Package, HIP (Package 402)

ACCESS TIME (ns)

22 = 25ns SRAM and 120ns FLASH
29 = 25ns SRAM and 90ns FLASH
27 = 25ns SRAM and 70ns FLASH

ORGANIZATION, 128K x 32

Flash PROM

SRAM

WHITE ELECTRONIC DESIGNS CORP.